



T16M35T600B(LS)

Triacs Silicon Bidirectional Thyristors

TRIACS 16 AMPERES RMS 600 VOLTS

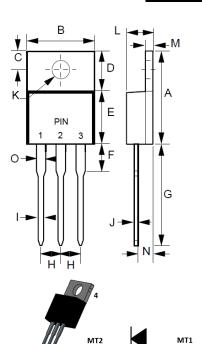
TO-220AB

FEATURES

- Blocking voltage to 600V
- Minimizes Snubber Networks for Protection
- On-State Current Rating of 16 Amperes RMS High surge Current Capability - 150 Amperes
- Glass Passivated Junctions for Reliability and Uniformity Operational in Three Quadrants, Q1, Q2, and Q3
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

MECHANICAL DATA

- Package: TO-220AB
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Terminals: Finish Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (c3)
- Weight: 0.07 ounces, 2.0 grams (Approximate)



TO-220AB DIM. MIN. MAX Α 14.22 15.88 В 9.65 10.67 С 2.54 3.43 D 5.84 6.86 Ε 8.26 9.28 F 6.35 G 12.70 14.73 н 2.29 2.79 Т 0.51 1.14 J 0.40 0.67 Κ 3.53Ø 4.09Ø 4.83 3.56 L Μ 1.40 1.14 Ν 2.03 2.92 0 1.17 1.37 All Dimensions in millimeter.

PIN ASSIGNMENT1Main terminal 12Main terminal 23Gate4Main terminal 2

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at +25°C ambient temperature unless otherwise specified.

MAXIMUM RATINGS

| PARAMETER | | VALUE | UNIT |
|--|---------------------|-------------|------------------|
| Peak repetitive off-state voltage (TJ = -40 to +125°C, sine wave, 50 to 60Hz; gate open) | Vdrm Vrrm | 600 600 | Volts |
| On-stage RMS current (full sine wave 50 to 60Hz, T_c = +80°C) | I _{T(RMS)} | 16 | Amp |
| Peak non-repetitive surge current (one full cycle 60Hz, T_J = +25°C) | Itsm | 150 | Amps |
| Circuit fusing consideration (t = 8.3ms) | l ² t | 93 | A ² s |
| Operating junction temperature range | TJ | -40 to +125 | °C |
| Storage temperature range | Тѕтс | -40 to +150 | °C |

Notes:

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



LITE-ON SEMICONDUCTOR

OFF CHARACTERISTICS

| PARAMETER | | SYMBOL | МАХ | UNIT |
|---|-------------------------|--------------|-------------|------|
| Peak repetitive forward or reverse blocking current (V_{AK} = rated V_{DRM} and V_{RRM} , gate open) | T」= +25°C T」= +125°C | Idrm Irrm | 0.01 2.0 | mA |

ON CHARACTERISTICS

| PARAMETER | SYMBOL | МАХ | UNIT |
|--|--|-------------------|-------|
| Peak forward on-state voltage ($I_{TM} = \pm 16A @ t_P \le 2.0ms$, duty cycle $\le 2\%$) | Vtm | 1.6 | Volts |
| Gate trigger current $(V_D = 12V, R_L = 100\Omega)$ | I _{GT1} IGT2 I _{GT3} | 35 35 35 | mA |
| Gate trigger voltage $(V_D = 12V, R_L = 100\Omega)$ | V _{GT1} V _{GT2} V _{GT3} | 1.5 1.5 1.5 | Volts |
| Holding current $(V_D = 12V, initiation current = \pm 150mA, gate open)$ | Ι _Η | 50 | mA |
| Latching current $(V_D = 12V, I_G = 35mA)$ | L1 L2 L3 | 50 80 50 | mA |

DYNAMIC CHARACTERISTICS

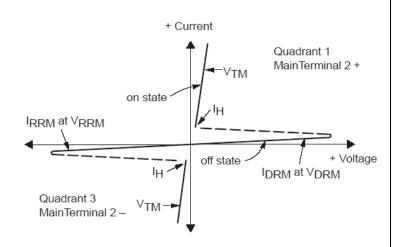
| PARAMETER | SYMBOL | MIN | UNIT |
|---|--------|-----|------|
| Critical rate of rise of Commutation voltage $V_D = 67\%$ rated V_{DRM} , exponential waveform, $T_C = +125$ °C | dv/dt | 600 | V/µs |



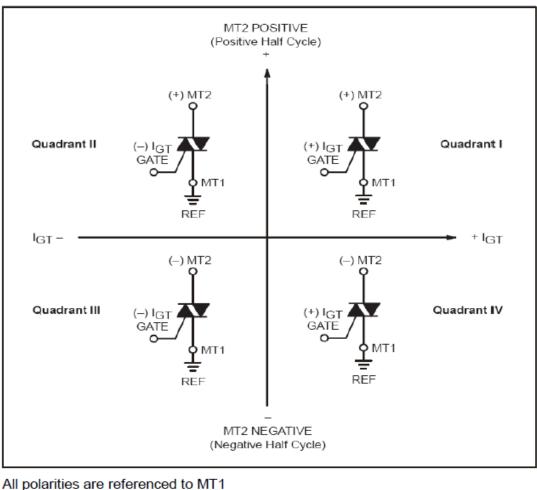
RATING AND CHARACTERISTIC CURVES T16M35T600B(LS)

LITE-ON SEMICONDUCTOR

| Symbol | Parameter |
|--------|---|
| VDRM | Peak Repetitive Forward Off State Voltage |
| IDRM | Peak Forward Blocking Current |
| VRRM | Peak Repetitive Reverse Off State Voltage |
| IRRM | Peak Reverse Blocking Current |
| VTM | Maximum On State Voltage |
| ΙΗ | Holding Current |



Quadrant Definitions

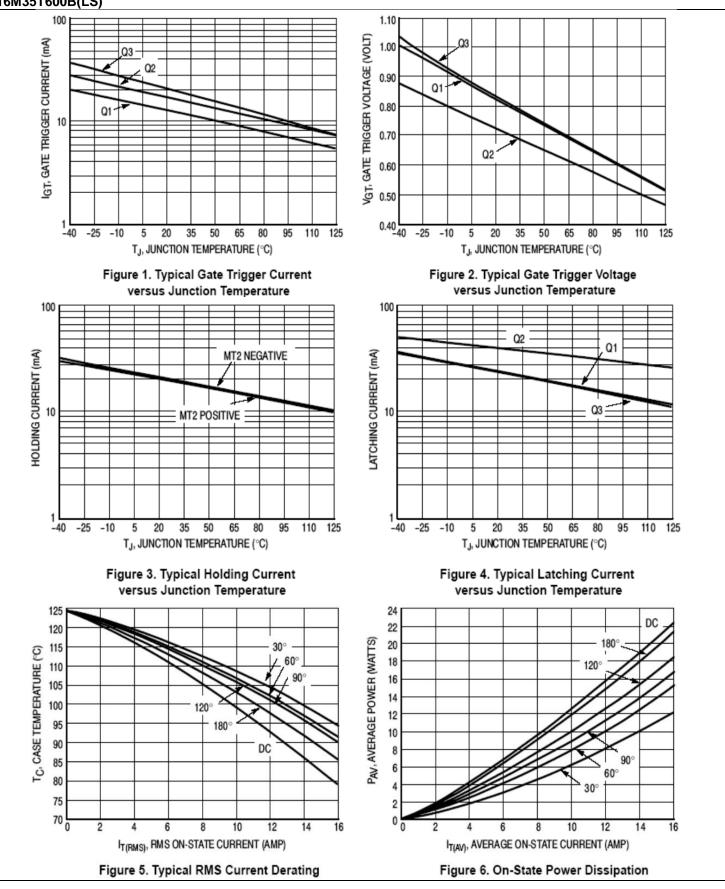


Whith in -phase signal (using standard AC lines) quadrants I and III are used



LITE-ON SEMICONDUCTOR

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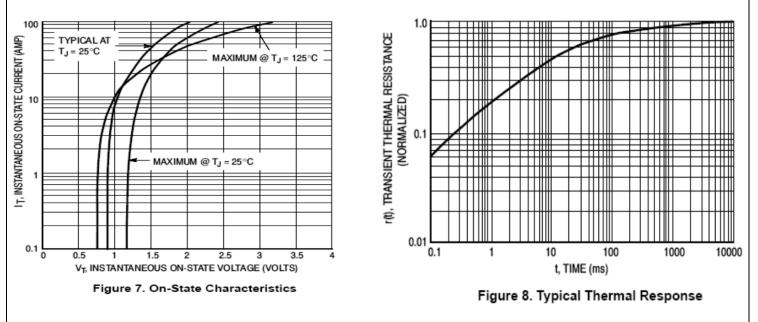




LITE-ON SEMICONDUCTOR

RATING AND CHARACTERISTIC CURVES

T16M35T600B(LS)

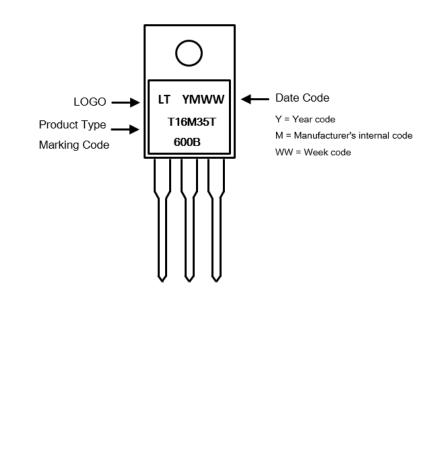




Ordering Information:

| Part Number | Package | Pac | king |
|---------------|----------|-------|---------|
| Fait Nulliger | Fackage | Qty. | Carrier |
| T16M35T600B | TO-220AB | 50pcs | Tube |

Marking Information:





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